

## Supporting information

### First-Principles Study of Interface Properties of CsSnI<sub>3</sub>-SnS heterostructure

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Table S1 Bandgaps (HSE06 functional) of SnS monolayer, CsI interface and SnI<sub>2</sub> interface at pre-contact state and contact state in the CsSnI<sub>3</sub>-SnS heterostructure.

	SnS-CsI		SnS-SnI <sub>2</sub>	
	SnS	CsI	SnS	SnI <sub>2</sub>
Pre-contact	2.08	1.48	2.18	1.68
Contact	1.92	1.46	2.39	1.28

Table S2 Comparison between the calculated and experimental values of the bandgap of CsSnI<sub>3</sub> and SnS

	calculated value		experiment value	Other calculated values
	PBE	HSE06		
CsSnI <sub>3</sub>	0.83	1.28	1.3 <sup>1</sup>	1.04 <sup>3</sup>
SnS	0.98	1.19	1.3 <sup>2</sup>	1.07 <sup>4</sup>

### References

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Fig. S1 The molecular dynamics simulation is calculated for the (a) CsI/SnS and (b) SnI<sub>2</sub>/SnS heterostructures at room temperature (300K).

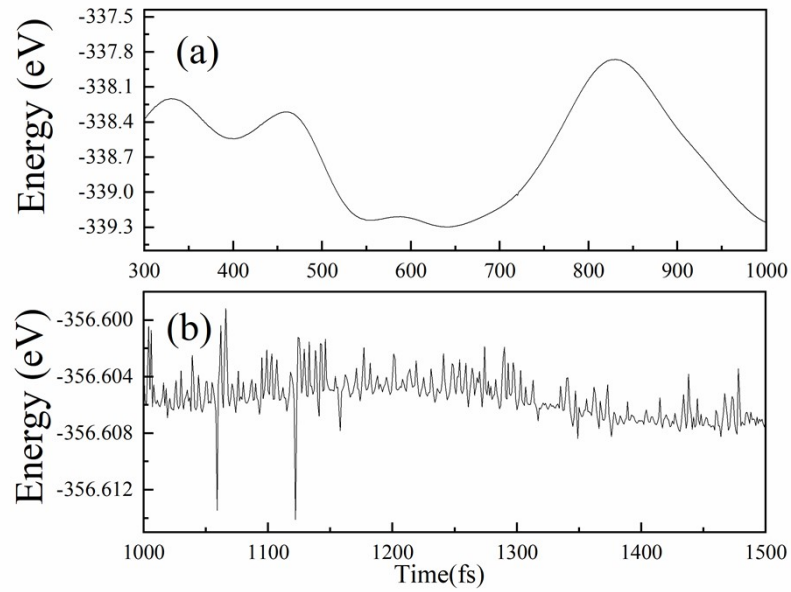


Fig. S2 Band structures of (a) CsI-SnS and (b) SnI<sub>2</sub>-SnS heterostructure. The blue and red lines denote the contribution from CsSnI<sub>3</sub> and SnS, respectively. The Fermi level is set at zero.

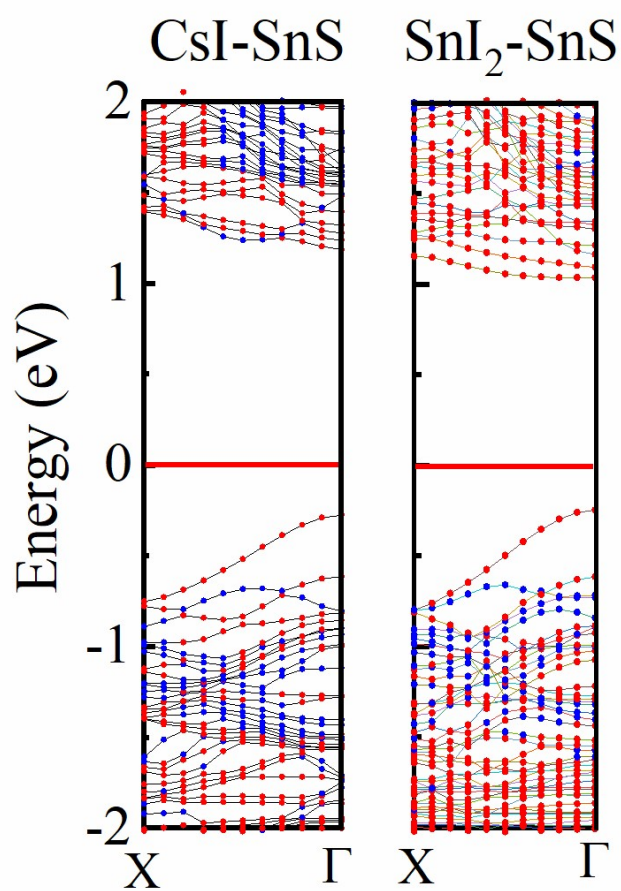


Fig. S3 The total density of states (DOS) of I, Sn, Cs, and S atoms of (a) CsI-SnS and (b) SnI<sub>2</sub>-SnS heterostructure. The DOS of interfacial atomic states of Sn and I in (c) CsI-SnS interface and Sn and S atom in SnI<sub>2</sub>-SnS interface.

